

T-31-23

**MOTOROLA  
SEMICONDUCTOR  
TECHNICAL DATA**

**The RF Line  
NPN Silicon  
RF Low Power Transistor**

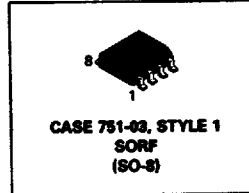
- ... designed for high current, low power amplifiers up to 2 GHz.
- High Current Gain-Bandwidth Product —  $f_T = 5.5$  GHz (Typ) @  $I_C = 75$  mA
- Low Noise — 2 dB (Typ) @ 500 MHz
- Low Intermodulation Distortion
- High Gain — 15.5 dB (Typ) @ 500 MHz
- Low Cost SORF Plastic Surface Mount Package
- State-of-the-Art Technology
  - Fine Line Geometry
  - Gold Top Metal and Wires
  - Silicon Nitride Passivated
  - Ion Implanted Arsenic Emitters
- Die Same as MRF581A

**MRF5812  
BF433\***

\*European Part Number

$I_C = 200$  mA  
SURFACE MOUNT  
HIGH FREQUENCY  
TRANSISTOR  
NPN SILICON

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**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	15	Vdc
Collector-Base Voltage	$V_{CBO}$	30	Vdc
Emitter-Base Voltage	$V_{EBO}$	2.5	Vdc
Collector-Current — Continuous	$I_C$	200	mAdc
Total Device Dissipation @ $T_C = 110^\circ\text{C}$ (1) Derate above $110^\circ\text{C}$	$P_D$	1.0 25	Watts mW/°C
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$ (2)	$P_D$	1.0 8.0	Watts mW/°C
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-65 to +150	°C

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	45	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	85	°C/W

**ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted.)**

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage ( $I_C = 5$ mAdc, $I_B = 0$ )	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Emitter Breakdown Voltage ( $I_C = 5$ mAdc, $V_{BE} = 0$ )	$V_{(BR)CES}$	30	—	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 0.1$ mAdc, $I_C = 0$ )	$V_{(BR)EBO}$	2.5	—	—	Vdc
Collector Cutoff Current ( $V_{CB} = 15$ Vdc, $V_{BE} = 0$ , $T_C = 25^\circ\text{C}$ )	$I_{CBO}$	—	—	0.1	mAdc

**ON CHARACTERISTICS**

DC Current Gain ( $I_C = 50$ mAdc, $V_{CE} = 10$ Vdc)	$h_{FE}$	30	90	200	—

(1) Case temperature is measured on the collector lead where the lead contacts the printed circuit board closest to the body of the package.  
(2) Free air.

(continued)

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**ELECTRICAL CHARACTERISTICS — continued** (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>DYNAMIC CHARACTERISTICS</b>					
Collector Base Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1 MHz)	C <sub>cb</sub>	—	1.2	2	pF
Current-Gain Bandwidth Product (1) (I <sub>C</sub> = 75 mA, V <sub>CE</sub> = 10 Vdc, f = 1 GHz)	f <sub>T</sub>	—	5.5	—	GHz
<b>FUNCTIONAL TESTS</b>					
Noise Figure (Minimum) (I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 Vdc, f = 0.5 GHz) Figure 4	NF <sub>MIN</sub>	—	2	—	dB
Noise Figure (50 Ohm Insertion) (I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 Vdc, f = 0.5 GHz) Figure 5	NF <sub>50 Ω</sub>	—	2.5	3	dB
Power Gain Associated with Noise Figure (I <sub>C</sub> = 50 mA, V <sub>CE</sub> = 10 Vdc, f = 0.5 GHz) Figure 5	S <sub>21</sub>   <sup>2</sup>	13	15.5	—	dB
Maximum Unilateral Gain (1) (I <sub>C</sub> = 75 mA, V <sub>CE</sub> = 10 Vdc, f = 0.5 GHz)	G <sub>Umax</sub>	—	17	—	dB
Intermodulation Distortion (2) Figure 1 (V <sub>CE</sub> = 10 V, I <sub>C</sub> = 75 mA, V <sub>out</sub> = +50 dBmV)	IMD(d3)	—	-65	—	dB

Notes: (1) Characterized on HP8542 Automatic Network Analyzer.  $G_{Umax} = \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)}$   
 (2) 2 Tones, f<sub>1</sub> = 497 MHz, f<sub>2</sub> = 503 MHz, 3rd Order Single Tone Reference.

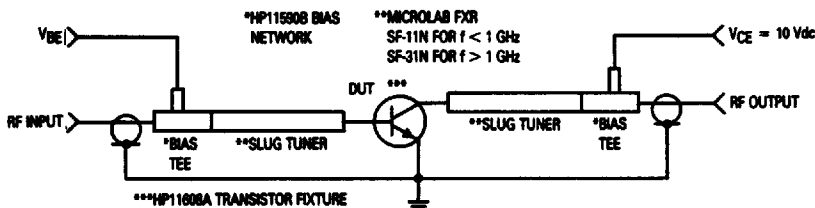


Figure 1. Functional Circuit Schematic

**TYPICAL CHARACTERISTICS**

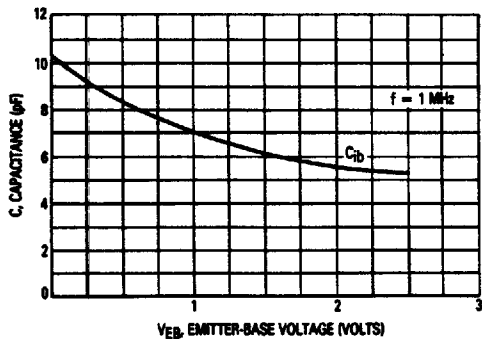


Figure 2. C<sub>cb</sub> Input Capacitance versus Voltage

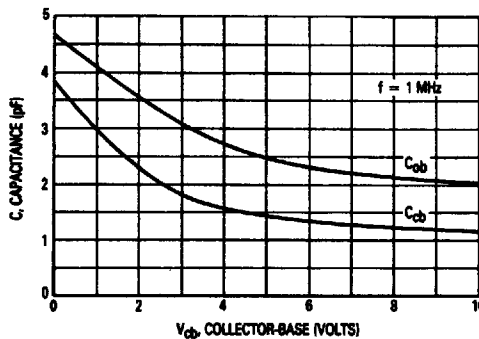


Figure 3. C<sub>cb</sub>, C<sub>cb</sub> Collector-Base Capacitance versus Voltage

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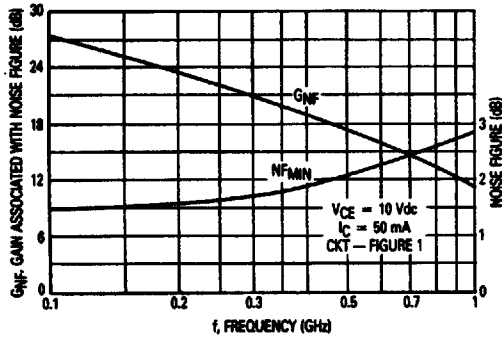


Figure 4. Noise Figure and Gain Associated with Noise Figure versus Frequency

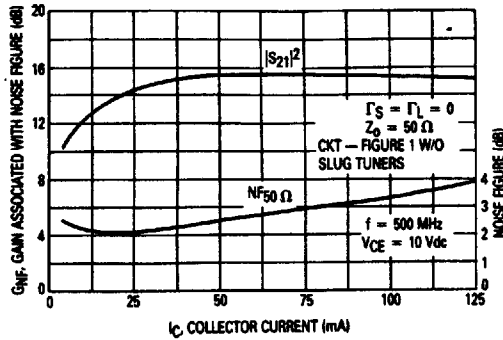


Figure 5. Noise Figure and Gain Associated with Noise Figure versus Collector Current

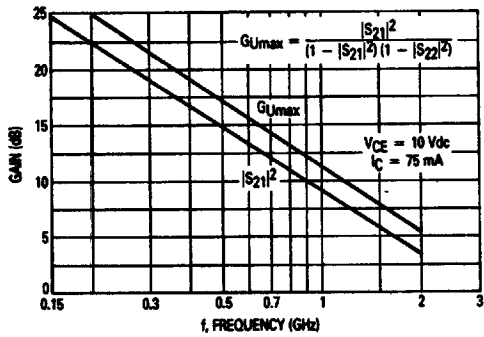


Figure 6.  $G_{Umax}$  — Maximum Unilateral Gain,  $|S_{21}|^2$  versus Frequency

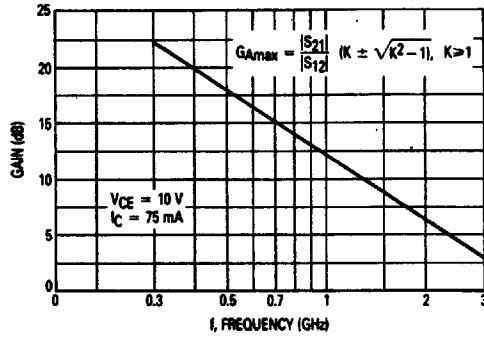


Figure 7.  $G_{Amax}$ , Maximum Available Gain versus Frequency

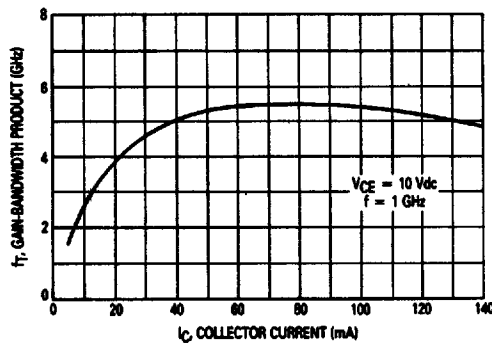


Figure 8. Gain-Bandwidth Product versus Collector Current

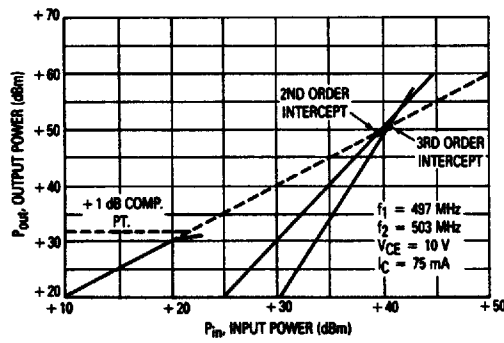


Figure 9. 2nd and 3rd Order Intercept Points and 1 dB Compression Point

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V <sub>CE</sub> (Volts)	I <sub>C</sub> (mA)	f (MHz)	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
			S <sub>11</sub>	∠φ	S <sub>21</sub>	∠φ	S <sub>12</sub>	∠φ	S <sub>22</sub>	∠φ
5	25	100	0.66	-123	18.3	118	0.04	43	0.53	-79
		300	0.66	-167	7	92	0.06	44	0.31	-120
		500	0.66	178	4.3	81	0.08	52	0.28	-133
		1000	0.62	154	2.2	63	0.13	61	0.28	-141
		2000	0.57	109	1.3	39	0.28	57	0.31	-148
		3000	0.55	68	1	23	0.41	41	0.34	-164
	50	100	0.64	-133	20.2	114	0.04	44	0.51	-93
		300	0.65	-171	7.6	91	0.06	50	0.34	-137
		500	0.65	175	4.6	81	0.08	56	0.31	-148
		1000	0.61	152	2.3	63	0.13	63	0.28	-149
		2000	0.56	109	1.3	39	0.28	57	0.3	-150
		3000	0.52	70	1	23	0.41	39	0.29	-169
	75	100	0.64	-137	20.8	113	0.04	44	0.5	-89
		300	0.66	-173	7.7	91	0.06	52	0.35	-142
		500	0.64	174	4.7	82	0.08	59	0.32	-154
		1000	0.61	151	2.4	65	0.14	64	0.3	-164
		2000	0.54	107	1.4	42	0.3	55	0.27	-167
		3000	0.52	69	1.1	24	0.42	37	0.25	-172
	100	100	0.64	-140	20.8	112	0.03	44	0.5	-103
		300	0.65	-174	7.6	90	0.06	53	0.36	-145
500		0.64	173	4.7	81	0.08	60	0.33	-156	
1000		0.61	151	2.4	65	0.15	64	0.31	-166	
2000		0.54	107	1.4	42	0.3	54	0.27	-169	
3000		0.52	65	1.1	24	0.42	37	0.25	-174	
10	25	100	0.65	-112	20.2	121	0.04	46	0.56	-62
		300	0.63	-162	8	93	0.05	46	0.29	-93
		500	0.62	-178	5	82	0.07	52	0.25	-102
		1000	0.6	157	2.5	63	0.11	63	0.26	-112
		2000	0.56	112	1.4	39	0.25	61	0.35	-125
		3000	0.55	69	1	23	0.39	47	0.4	-146
	50	100	0.63	-122	22.9	117	0.03	46	0.5	-74
		300	0.62	-167	8.6	92	0.06	51	0.28	-112
		500	0.6	178	5.3	82	0.07	58	0.24	-122
		1000	0.58	154	2.7	64	0.12	65	0.23	-129
		2000	0.51	111	1.5	40	0.26	59	0.28	-132
		3000	0.5	70	1.2	24	0.39	44	0.34	-144
	75	100	0.63	-126	23.8	116	0.03	46	0.49	-80
		300	0.63	-168	9	92	0.05	51	0.28	-120
		500	0.62	177	5.5	82	0.07	58	0.24	-130
		1000	0.58	154	2.8	65	0.12	65	0.23	-137
		2000	0.52	111	1.5	41	0.26	58	0.27	-135
		3000	0.5	70	1.2	24	0.39	42	0.32	-146
	100	100	0.62	-128	23.8	114	0.03	46	0.46	-82
		300	0.62	-169	8.9	91	0.05	54	0.26	-120
500		0.6	176	5.4	81	0.07	61	0.23	-130	
1000		0.57	152	2.8	64	0.12	66	0.21	-136	
2000		0.51	109	1.5	40	0.27	59	0.26	-134	
3000		0.5	68	1.2	24	0.39	43	0.32	-145	
15	25	100	0.66	-106	21	123	0.03	47	0.57	-54
		300	0.63	-159	8.5	94	0.05	46	0.3	-77
		500	0.61	-177	5.2	82	0.06	52	0.26	-84
		1000	0.58	156	2.6	62	0.11	64	0.28	-96
		2000	0.54	110	1.4	36	0.23	63	0.39	-115
		3000	0.56	68	1	22	0.37	49	0.46	-137
	50	100	0.62	-114	24	119	0.03	46	0.51	-64
		300	0.6	-163	9.2	93	0.05	51	0.26	-92
		500	0.59	-179	5.7	81	0.07	58	0.22	-100
		1000	0.56	154	2.9	63	0.12	66	0.23	-109
		2000	0.52	109	1.5	39	0.25	60	0.32	-118
		3000	0.52	67	1.1	22	0.37	46	0.39	-137
	75	100	0.62	-118	24.6	117	0.03	46	0.48	-67
		300	0.59	-165	9.4	92	0.05	53	0.24	-96
		500	0.58	179	5.7	81	0.07	60	0.21	-104
		1000	0.56	154	2.9	63	0.12	66	0.22	-111
		2000	0.5	109	1.5	38	0.25	60	0.31	-118
		3000	0.52	67	1.1	22	0.37	46	0.38	-136
	100	100	0.62	-121	24.8	116	0.03	46	0.46	-68
		300	0.6	-166	9.3	91	0.05	53	0.23	-96
500		0.58	179	5.7	81	0.07	61	0.2	-102	
1000		0.56	155	2.9	63	0.12	66	0.22	-109	
2000		0.5	111	1.5	39	0.25	62	0.32	-117	
3000		0.5	68	1.1	23	0.37	47	0.39	-136	

Figure 10. Common Emitter S-Parameters